

2SC5472

Silicon NPN epitaxial planer type

For low-voltage low-noise high-frequency oscillation

■ Features

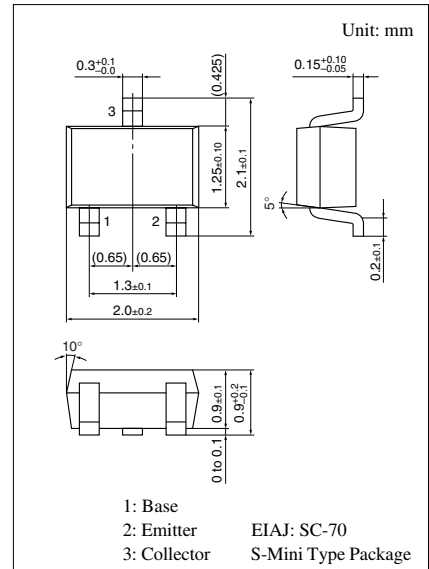
- High transition frequency f_T
- High gain of 8.2 dB and low noise of 1.8 dB at 3 V
- Optimum for RF amplification of a portable telephone and pager
- S-mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	9	V
Collector to emitter voltage	V_{CEO}	6	V
Emitter to base voltage	V_{EBO}	1	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 9\text{ V}, I_E = 0$			1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$			1	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}$	80		200	
Transition frequency	f_T	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$		12.0		GHz
Collector output capacitance	C_{ob}	$V_{CB} = 3\text{ V}, I_E = 0, f = 1\text{ MHz}$		0.6	0.9	pF
Forward transfer gain	$ S_{21c} ^2$	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$	6.0	8.0		dB
Noise figure	NF	$V_{CE} = 3\text{ V}, I_C = 3\text{ mA}, f = 1.5\text{ GHz}$		1.8	3.0	dB



Marking Symbol: 3A

